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(71)Applicant : **SEIKO EPSON CORP**

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(72)Inventor : **HORIE TOMOKAZU  
SUGIYAMA SHINICHI**

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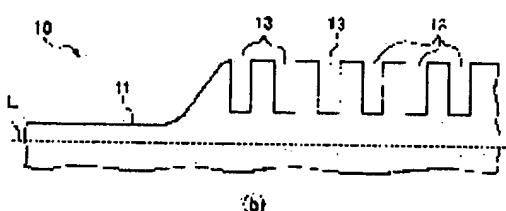
## **(54) PLANARIZATION METHOD AND METHOD FOR MANUFACTURING SEMICONDUCTOR DEVICE**

**(57)Abstract:**

**PROBLEM TO BE SOLVED:** To provide a pretreatment method for planarization, by which unpolished parts and dishing can be reduced, even if a large area having little irregularities is included and a more uniform planarization level can be realized with a small amount of polishing, and to provide a method for manufacturing semiconductor devices.



**SOLUTION:** A substrate has a first area and a second area larger than the first area. Trenches are formed between the first and second areas for separating them and an insulation film is formed on the substrate and in the trenches. A dummy pattern, having plural irregularities, is formed on the insulating film on the second area. After that, the insulation film is planarized through chemical and mechanical polishing.



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## **LEGAL STATUS**

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